

JAW EC-400 (Woolam Spectroscopic)																				Brian Lingg, PM			
Date	User	Film	Recipe	Substrate T	Thickness	Dep.time	Water center	Index @ 632.8nm	Index @ 1550nm	Dep.rate	Stress	HF etch rate wafer	LPD (light point defects)	AVG dep.rate	AVG+10%	AVG-10%	AVG index@	AVG+2%	AVG-2%	AVG.Stress	AVG+10%	AVG-10%	Additional Notes
				250 °C	(Å)	sec		(nm/min)	(nm/min)	Mpa	(nm/min)	before dep.	after dep.										
1/1/2012	User	SIN	SIN_10	250 °C																			Deposition done on 4" Si wafer
01/06/14	Biljana	SIN	SIN_10	250	1055.25	568.1	1.949	1.899	11.15	571.87	78	547	78	11.21	12.33	10.09	1.938	1.977	1.899	508.86	610.63	407.09	
01/23/14	Biljana	SIN	SIN_10	250	1133.40	568.1	1.935	1.890	11.97	446.98	90.66	137	377	11.21	12.33	10.09	1.938	1.977	1.899	508.86	610.63	407.09	1/23/14
02/03/14	Biljana	SIN	SIN_10	250	1046.60	568.1	1.937	1.893	11.05	486.75	81.21	322	604	11.21	12.33	10.09	1.938	1.977	1.899	508.86	610.63	407.09	
02/19/14	Biljana	SIN	SIN_10	250	1030.66	568.1	1.935	1.890	10.89	353.92	77.32	75	323	11.21	12.33	10.09	1.938	1.977	1.899	508.86	610.63	407.09	2/14/14 Silane change
03/14/14	Biljana	SIN	SIN_10	250	1042.16	568.1	1.933	1.887	11.01	684.87	92.89	37	122	11.21	12.33	10.09	1.938	1.977	1.899	508.86	610.63	407.09	

Avg.Thickness	1061.614
Avg. Index	1.938
Avg Dep. Rate	11.21
Avg+2%	1.977
Avg+10%	12.33
Avg-2%	1.899
Avg-10%	10.09
Avg. Stress	508.86
Avg +20%	610.63
Avg -20%	407.09
Avg. HF e.r.	85.52

